

N-Ch 100V Fast Switching MOSFETs
Applications

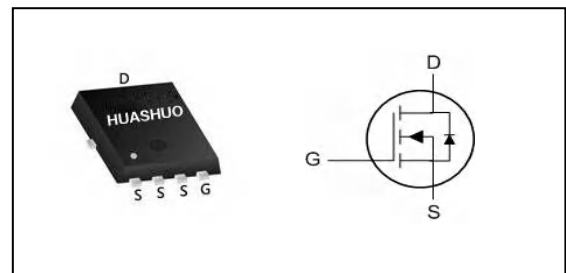
- Portable Equipment.
- Battery Powered Systems.
- Hard Switching and High-Speed Circuit.

Product Summary

V_{DS}	100	V
$R_{DS(ON),TYP}$	25	m Ω
I_D	25	A

Features

- 100% EAS Guaranteed
- Low $R_{DS(ON)}$
- Low Gate Charge
- RoHs and Halogen-Free Compliant
- Advance SGT MOS Technology

PRPAK3*3 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current ¹	25	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current ¹	15	A
I_{DM}	Pulsed Drain Current ²	100	A
EAS	Single Pulse Avalanche Energy ³	60	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	28	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	55	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4.5	$^{\circ}C/W$

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Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=10A$	---	25	30	$m\Omega$
	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V$, $I_D=10A$	---	30	40	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	1.5	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=100V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	0.6	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=10A$	---	16	---	nC
Q_{gs}	Gate-Source Charge		---	4.8	---	
Q_{gd}	Gate-Drain Charge		---	2.2	---	
$T_d(on)$	Turn-On Delay Time	$V_{DD}=30V$, $V_{GS}=10V$, $R_G=6\Omega$, $I_D=1A$	---	7	---	ns
T_r	Rise Time		---	8	---	
$T_d(off)$	Turn-Off Delay Time		---	21	---	
T_f	Fall Time		---	3	---	
C_{iss}	Input Capacitance	$V_{DS}=50V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	590	---	pF
C_{oss}	Output Capacitance		---	175	---	
C_{rss}	Reverse Transfer Capacitance		---	9	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5,6}	$V_G=V_D=0V$, Force Current	---	---	25	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=10A$, $dI/dt=100A/\mu s$, $T_J=25^{\circ}\text{C}$	---	30	---	nS
Q_{rr}	Reverse Recovery Charge		---	135	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.5mH$

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

6.The maximum current rating is package limited.

Typical Characteristics

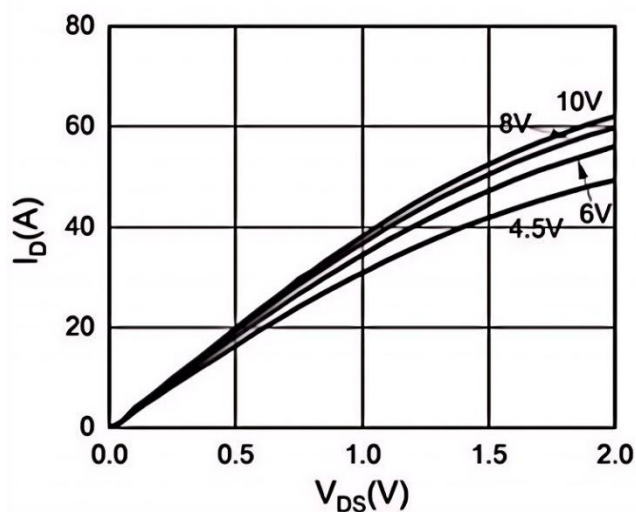


Fig.1 Typical Output Characteristics

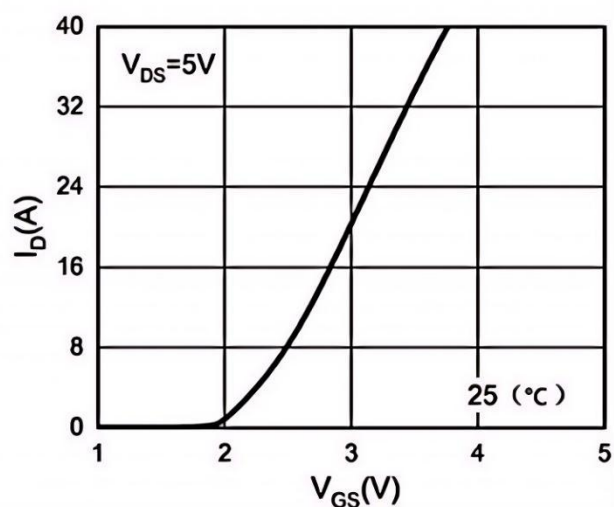


Fig.2 Transfer Characteristics

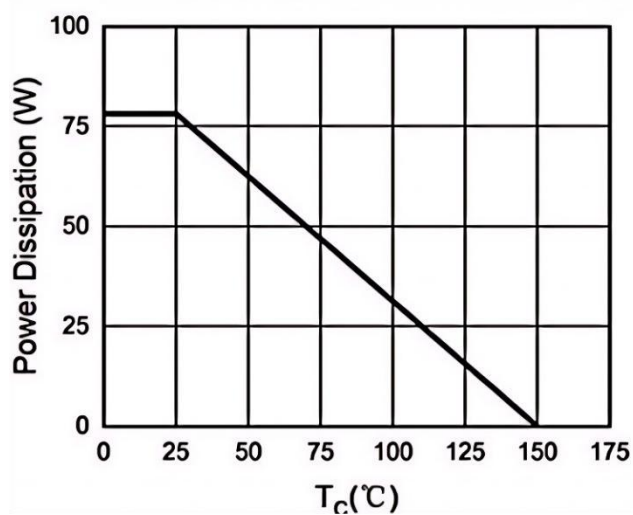


Fig.3 Power Dissipation

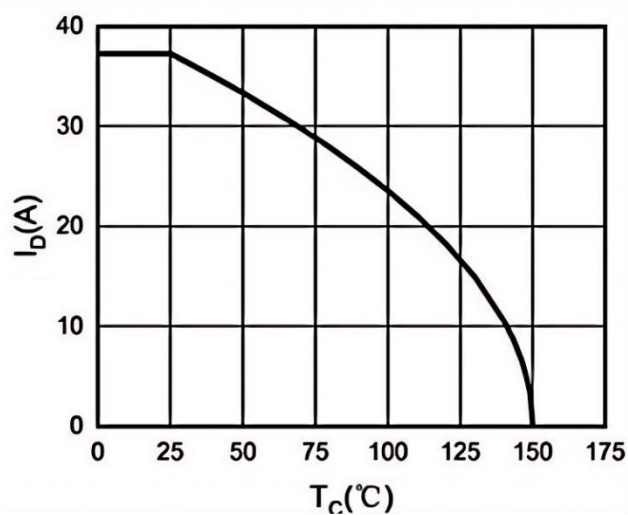


Fig.4 Drain Current

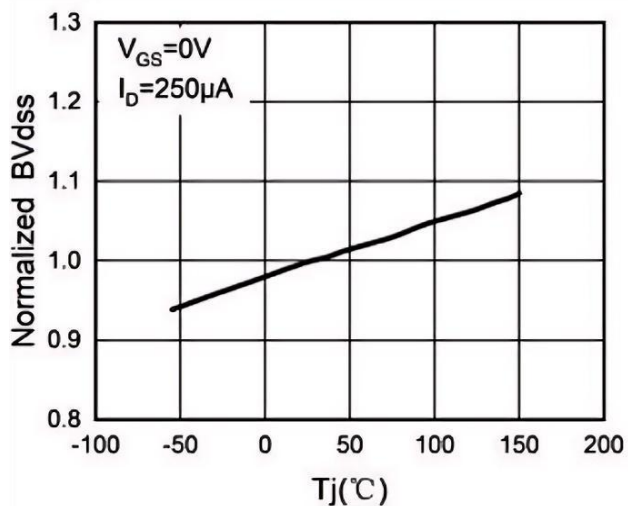


Fig.5 BV_{DS} vs Junction Temperature

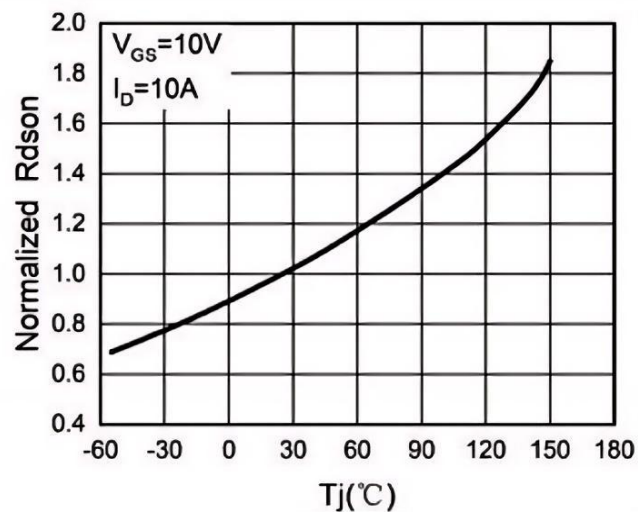


Fig.6 $R_{DS(ON)}$ vs Junction Temperature



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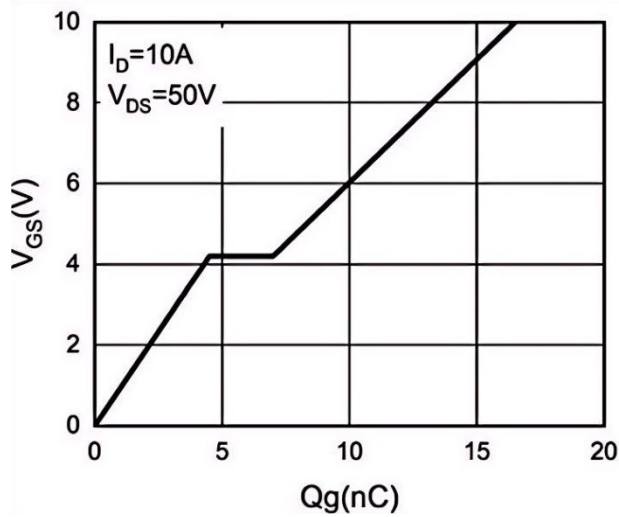


Fig.7 Gate Charge Waveforms

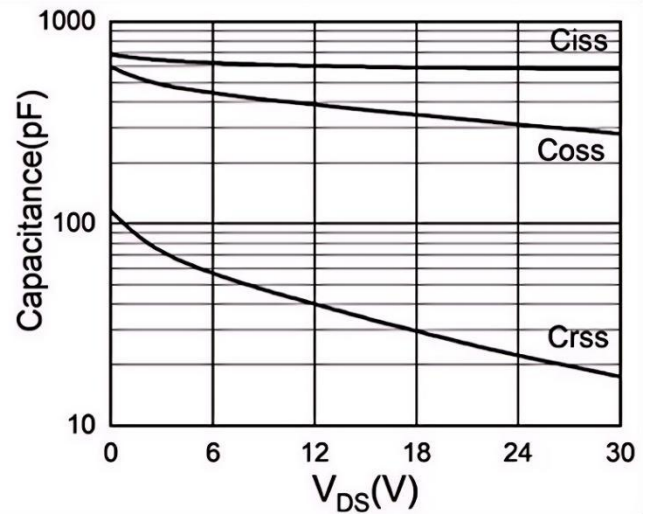


Fig.8 Capacitance

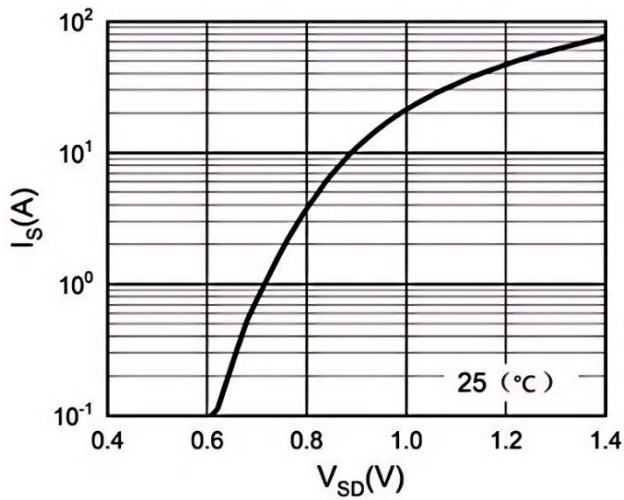


Fig.9 Body Diode Characteristics

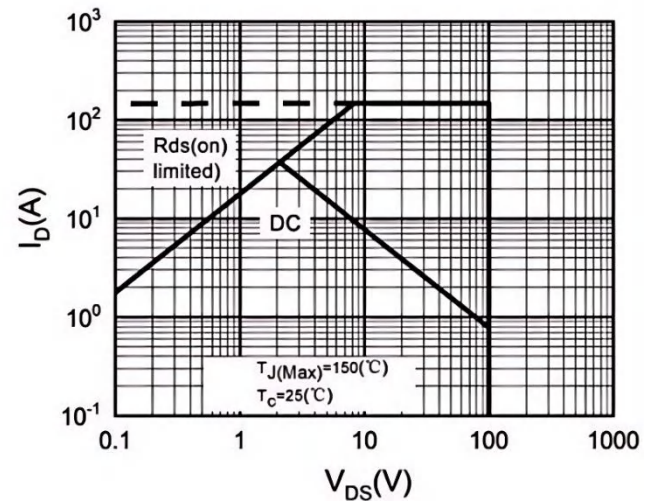
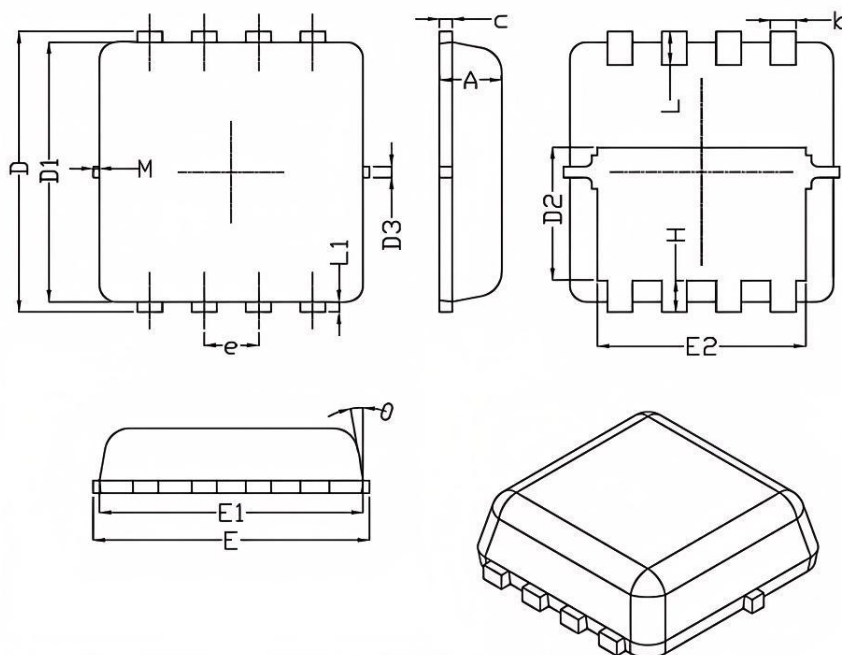


Fig.10 Maximum Safe Operating Area

Ordering Information

Part Number	Package code	Packaging
HSBB0098	PRPAK3*3	3000/Tape&Reel

PRPAK3*3(E) Single Package Outline



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
C	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.15	3.30	3.45
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

HSBB0098 Marking:

